• High Speed

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

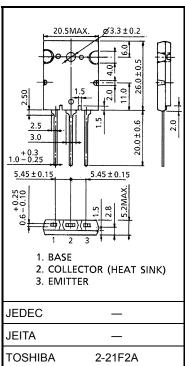
# **2SC5859**

#### HORIZONTAL DEFLECTION OUTPUT FOR HDTV, DIGITAL TV, PROJECTION TV

- High Voltage : VCBO = 1700 V
- Low Saturation Voltage : VCE (sat) = 3 V (max)
  - $: t_{f(2)} = 0.1 \ \mu s \ (Typ.)$

CHARACTERISTIC		SYMBOL	RATING	UNIT					
Collector-Base Voltage		V <sub>CBO</sub>	1700	V					
Collector-Emitter Voltage		V <sub>CEO</sub>	750	V					
Emitter-Base Voltage		V <sub>EBO</sub>	5	V					
Collector Current	DC	Ι <sub>C</sub>	23	A					
	Pulse	I <sub>CP</sub>	46						
Base Current		Ι <sub>Β</sub>	11.5	A					
Collector Power Dissipation		PC	210	W					
Junction Temperature		Тj	150	°C					
Storage Temperature Range		T <sub>stg</sub>	-55~150	°C					





Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

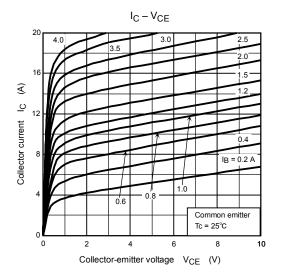
Weight: 9.75 g (typ.)

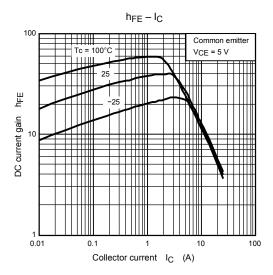
temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

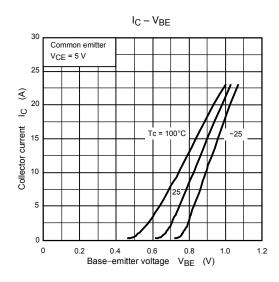
### ELECTRICAL CHARACTERISTICS (Tc = 25°C)

CHARACTER	RISTIC	SYMBOL	TEST CONDITION	Min	Тур.	Max	UNIT
Collector Cut-off Curre	ent	I <sub>CBO</sub>	V <sub>CB</sub> = 1700 V, I <sub>E</sub> = 0	_	_	1	mA
Emitter Cut-off Curren	t	I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	—	—	100	μA
Collector – Emitter Breakdown Voltage		V (BR) CEO	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	750	_	_	V
DC Current Gain		h <sub>FE (1)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 2 A	20	—	55	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 8 A	10	_	22	
		h <sub>FE (3)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 18 A	4.5	_	8	
Collector-Emitter Satu	ration Voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 18 A, I <sub>B</sub> = 4.5 A	_	_	3	V
Base-Emitter Saturation	on Voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = 18 A, I <sub>B</sub> = 4.5 A	—	1.0	1.5	V
Transition Frequency		f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 0.1 A	_	2	_	MHz
Collector Output Capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	320	_	pF
Switching Time	Storage Time	t <sub>stg(1)</sub>	I <sub>CP</sub> = 8 A , I <sub>B1</sub> (end) = 1 A	_	4	_	μs
	Fall Time	t <sub>f(1)</sub>	$f_{\rm H} = 32 \text{ kHz}$	_	0.15	_	
	Storage Time	t <sub>stg(2)</sub>	I <sub>CP</sub> = 7.5 A, I <sub>B1</sub> (end) = 1 A	_	1.8	_	- µs
	Fall Time	t <sub>f(2)</sub>	f <sub>H</sub> = 100 kHz	—	0.1	—	

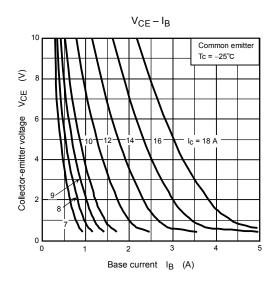
## **TOSHIBA**

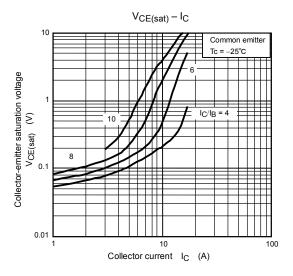


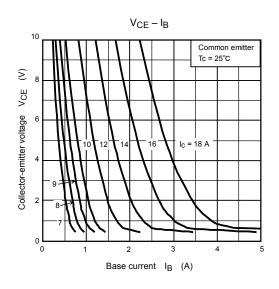


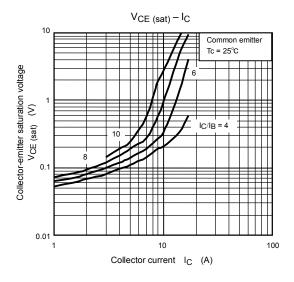


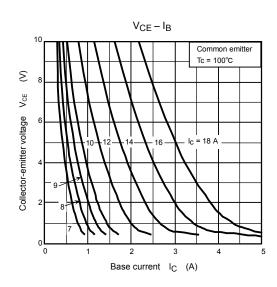
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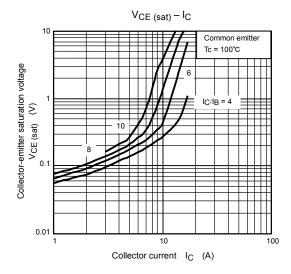


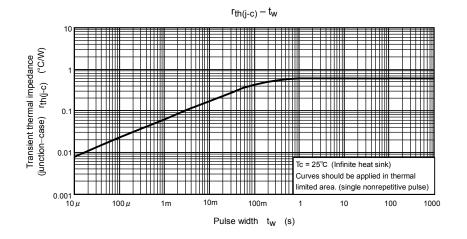


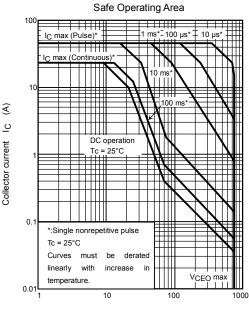




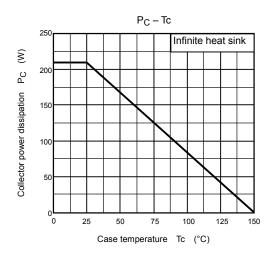




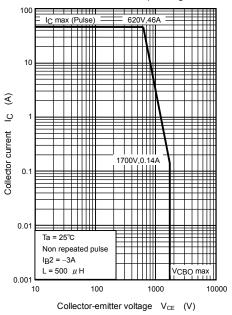




Collector-emitter voltage  $V_{CE}$  (V)



Reverse Bias - Safe Operating Area



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